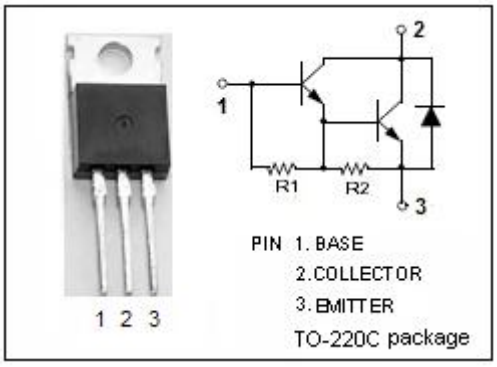
isc Silicon NPN Darlington Power Transistor 2SC1880

DESCRIPTION

- High DC Current Gain
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 120V(Min)
- Low Collector-Emitter Saturation Voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

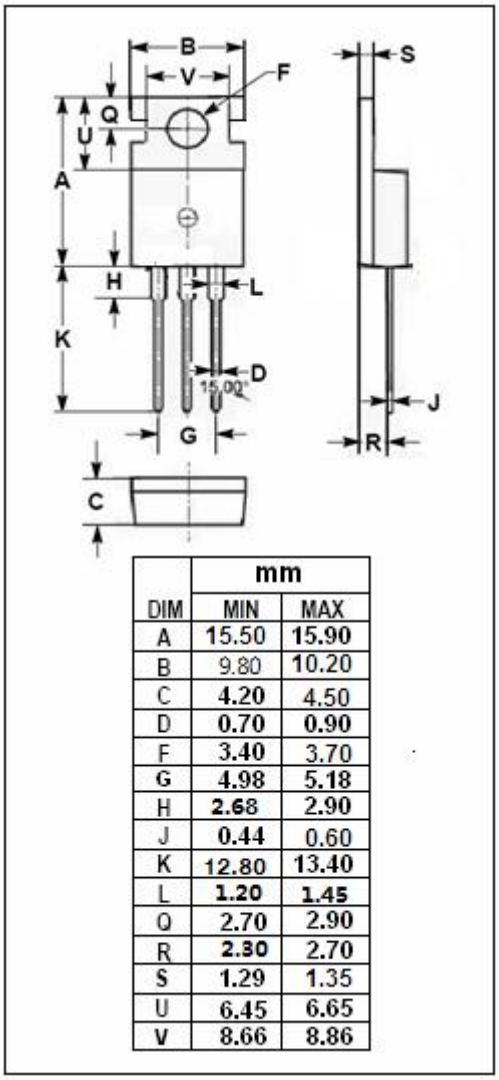
- Designed for general purpose amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current	120	mA
P_C	Collector Power Dissipation T_C=25℃	65	W
	Collector Power Dissipation T_a=25℃	2	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.92	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 30mA, I_B= 0	120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2A ,I_B= 8mA			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V, I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			2	mA
h_{FE}	DC Current Gain	I_C= 2A ; V_{CE}= 2V	1000			